

AMENDMENTS

In the Specification:

Please amend the following paragraphs as follows.

[Para 9] With the transparent ~~δ -shift~~ π -shift end portion of the isolated linear pattern on the photomask, the line-end shortening effect of the resulting isolated linear photoresist pattern can be reduced. Meanwhile, the transparent ~~$\delta/2$ -shift~~ $\pi/2$ -shift region located adjacent to the ends of the dense linear patterns on the photomask can reduce the line-end shortening effect of the resulting dense linear photoresist patterns.

[Para 18] To demonstrate the effects of this invention, some simulations have been made to derive the LES values of the isolated/dense photoresist line patterns obtained by using a conventional HT photomask of FIG. 1 and the phase shift photomask of FIG. 2, respectively. As the common parameters used in the simulations, the wavelength of the exposure light is 193nm, the line/space width is 90/90nm, and the gap width (G) between every two opposite line patterns is 100nm. In addition, the length "L" of the transparent ~~δ -shift~~ π -shift end portion 210a of each isolated line pattern 210 is 200nm. The results of the simulations are listed in Table I.

[Para 19] As shown in Table I, with the transparent ~~δ -shift~~ π -shift end portion of an isolated linear pattern on the photomask, the line-end shortening of the resulting isolated photoresist line pattern can be significantly reduced, even when the substrate is exposed at a defocused position in the exposure process. Meanwhile, the transparent ~~$\delta/2$ -shift~~ $\pi/2$ -shift region located adjacent to the ends of the dense line patterns can reduce the line-end shortening of the resulting dense photoresist line patterns, even when the substrate is exposed at a defocused position in the exposure process.